	117.	Garage Mout	DB ·	Time stamp
L Number	Hits	Search Text buried near10 source near10 drain	USPAT;	2003/03/06 17:02
1	1533	burled healto source healto diain	US-PGPUB	
2	2119	buried with source with drain	USPAT; US-PGPUB	2003/03/06 17:03
3	2119	(buried near10 source near10 drain) (buried with source with drain)	USPAT; US-PGPUB	2003/03/06 16:16
4	444	((buried near10 source near10 drain) (buried with source with drain)) and ((single mono) near3 crystal\$6)	USPAT; US-PGPUB	2003/03/06 17:03
9 .	661	buried near10 source near10 drain	EPO; JPO; DERWENT; IBM TDB	2003/03/06 17:03
10	1095	buried with source with drain	EPO; JPO; DERWENT; IBM TDB	2003/03/06 17:03
11	1095	(buried near10 source near10 drain) (buried with source with drain)	EPO; JPO; DERWENT; IBM TDB	2003/03/06 17:03
12	43	((buried near10 source near10 drain) (buried with source with drain)) and ((single mono) near3 crystal\$6)	EPO; JPO; DERWENT; IBM TDB	2003/03/06 17:03
_	495266	dielectric insulat\$3	USPAT; US-PGPUB	2002/09/07 19:26
_	87316	(dielectric insulat\$3) and gate	USPAT; US-PGPUB	2002/09/07 19:26
_	16217	((dielectric insulat\$3) and gate) and spacer	USPAT; US-PGPUB	2002/09/07 19:26
_	15506	(((dielectric insulat\$3) and gate) and spacer) and (recess open\$3 hole via contact trench)	USPAT; US-PGPUB	2002/09/07 19:33
	1634	((((dielectric insulat\$3) and gate) and spacer) and (recess open\$3 hole via contact trench)) and (isotropic\$5 near5	USPAT	2002/09/07 19:27
-	241	etch\$3) ((((dielectric insulat\$3) and gate) and spacer) and (recess open\$3 hole via contact trench)) and (isotropic\$5 near5	US-PGPUB	2002/09/07 19:20
_	946251	etch\$3) dielectric insulat\$3	EPO; JPO; DERWENT;	2002/09/07 19:26
_	72774	(dielectric insulat\$3) and gate	IBM_TDB EPO; JPO; DERWENT; IBM TDB	2002/09/07 19:26
-	3911	((dielectric insulat\$3) and gate) and spacer	EPO; JPO; DERWENT; IBM TDB	2002/09/07 19:26
_	2227	(((dielectric insulat\$3) and gate) and spacer) and (recess open\$3 hole via contact trench)	EPO; JPO; DERWENT; IBM TDB	2002/09/07 19:27
-	48	<pre>((((dielectric insulat\$3) and gate) and spacer) and (recess open\$3 hole via contact trench)) and (isotropic\$5 near5 etch\$3)</pre>	EPO; JPO; DERWENT; IBM_TDB	2002/09/07 19:31
	48244	(source drain) same junction	USPAT; US-PGPUB	2002/09/07 19:59
_	1526	((source drain) same junction) and ((silicon near5 germanium) SiGe)	USPAT; US-PGPUB	2002/09/07 19:59
-	1446	(((source drain) same junction) and ((silicon near5 germanium) SiGe)) and (recess open\$3 hole via contact trench)	USPAT; US-PGPUB	2002/09/07 19:34
_	1278	(((source drain) same junction) and ((silicon near5 germanium) SiGe)) and	USPAT	2002/09/07 19:59
-	14097	(recess open\$3 hole via contact trench) (source drain) same junction	EPO; JPO; DERWENT;	2002/09/07 19:59
_	425	"19" and ((silicon near5 germanium) SiGe)	IBM_TDB EPO; JPO; DERWENT; IBM TDB	2002/09/07 19:59
	L			

				100 (00 00 00
	97	("19" and ((silicon near5 germanium)	EPO; JPO;	2002/09/07 20:00
		SiGe)) and (recess open\$3 hole via contact	DERWENT;	}
	1	trench)	IBM_TDB	
_	26288		USPAT;	2003/03/06 11:54
_	20200	(Space and a series of series and series of series and series of s	US-PGPUB	
_	3816	((spacer same (gate electrode))) and	USPAT;	2003/03/06 11:54
	3323	(anisotropic\$3 same etch\$3 same spacer)	US-PGPUB	
_	2013	(((spacer same (gate electrode))) and	USPAT;	2003/03/06 11:54
		(anisotropic\$3 same etch\$3 same spacer))	US-PGPUB	
		and ((recess open\$3 hole) same substrate)		
_	76	((((spacer same (gate electrode))) and	USPAT;	2003/03/06 11:54
		(anisotropic\$3 same etch\$3 same spacer))	US-PGPUB	
		and ((recess open\$3 hole) same substrate)		1
) and ((dop\$4 same ((single mono) near3		
		crystal\$6)) same (recess open\$3 hole))		2003/03/06 11:54
-	17277	(spacer same (gate electrode))	EPO; JPO;	2003/03/06 11:34
			DERWENT;	
			IBM_TDB	2003/03/06 11:54
-	380	((spacer same (gate electrode))) and	EPO; JPO;	2003/03/06 11:54
		(anisotropic\$3 same etch\$3 same spacer)	DERWENT;	
			IBM_TDB	2003/03/06 11:54
-	1		EPO; JPO;	2003/03/00 11.34
		(anisotropic\$3 same etch\$3 same spacer))	DERWENT;	
	1	and ((recess open\$3 hole) same substrate)	IBM_TDB	
) and ((dop\$4 same ((single mono) near3		
1		crystal\$6)) same (recess open\$3 hole))	EPO; JPO;	2003/03/06 11:55
-	83	(((spacer same (gate electrode))) and	DERWENT;	2003/03/00 11.33
		(anisotropic\$3 same etch\$3 same spacer))	IBM TDB	
1		and ((recess open\$3 hole) same substrate)	TDM TDD	<u> </u>